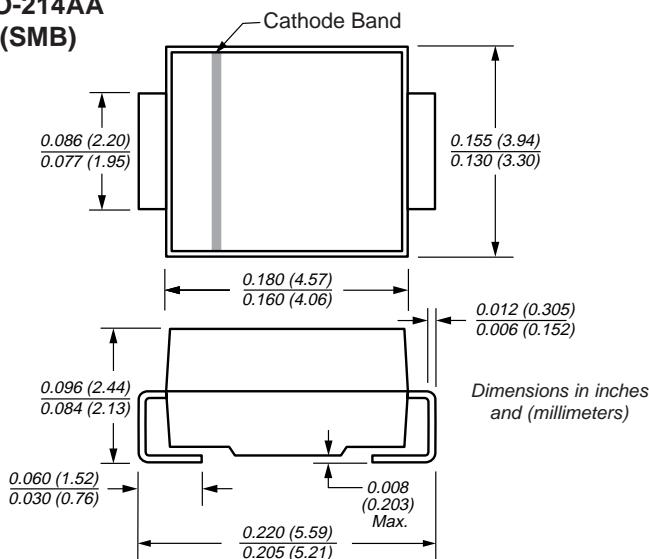
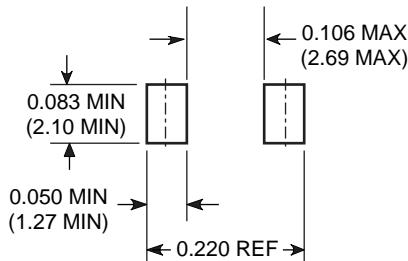




High Voltage Surface Mount Schottky Barrier Rectifiers

 Reverse Voltage 90 to 100V
 Forward Current 2.0A

**DO-214AA
(SMB)**

Mounting Pad Layout

Mechanical Data

Case: JEDEC DO-214AA molded plastic body
Terminals: Solder plated, solderable per MIL-STD750,
 Method 2026
Polarity: Color band denotes cathode end
Weight: 0.003oz., 0.093g

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Low profile surface mount package
- Built-in strain relief
- Low power loss, high efficiency
- For use in low voltage high frequency inverters, free wheeling, and polarity protection applications
- Guardring for overvoltage protection
- High temperature soldering guaranteed:
 250°C/10 seconds at terminals

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

| Parameter | Symbol | SS2H9 | SS2H10 | Unit |
|--|-----------------------------------|-------------|--------|------|
| Device marking code | | MS9 | MS10 | |
| Maximum repetitive peak reverse voltage | V _{RRM} | 90 | 100 | V |
| Working peak reverse voltage | V _{RWM} | 90 | 100 | V |
| Maximum DC blocking voltage | V _{DC} | 90 | 100 | V |
| Maximum average forward rectified current at: T _L = 130°C | I _{F(AV)} | 2.0 | | A |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | I _{FSM} | 75 | | A |
| Peak repetitive reverse surge current at t _p = 2.0μs, 1KHz | I _{RRM} | 1.0 | | A |
| Critical rate of rise of reverse voltage | dV/dt | 10,000 | | V/μs |
| Maximum thermal resistance junction to lead T _L = 25°C | R _{θJL} | 25 | | °C/W |
| Operating junction and storage temperature range | T _J , T _{STG} | -65 to +175 | | °C |

Electrical Characteristics (TA = 25°C unless otherwise noted)

| | | | | |
|--|---|----------------|--------------|----------|
| Maximum instantaneous forward voltage at (Note 1): | I _F = 2.0A, T _J = 25°C I _F = 2.0A, T _J = 125°C | V _F | 0.79 0.65 | V |
| Maximum DC reverse current at rated DC blocking voltage (Note 1) | T _J = 25°C T _J = 125°C | I _R | 10 4 | μA mA |

Note: (1) Pulse test: 300μs pulse width, 1% duty cycle

SS2H9 and SS2H10

Vishay Semiconductors
formerly General Semiconductor



Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Forward Current Derating Curve

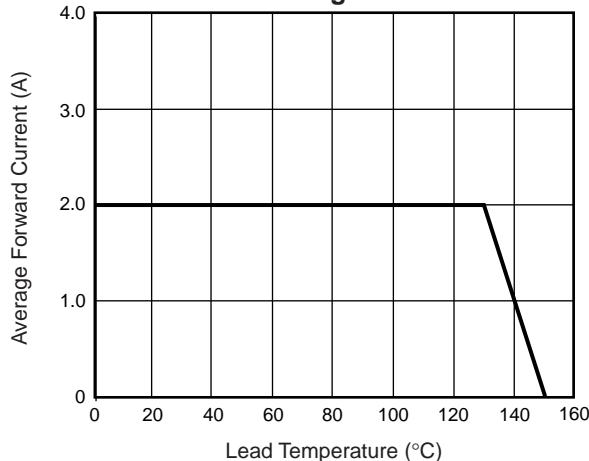


Fig. 2 – Typical Instantaneous Forward Characteristics

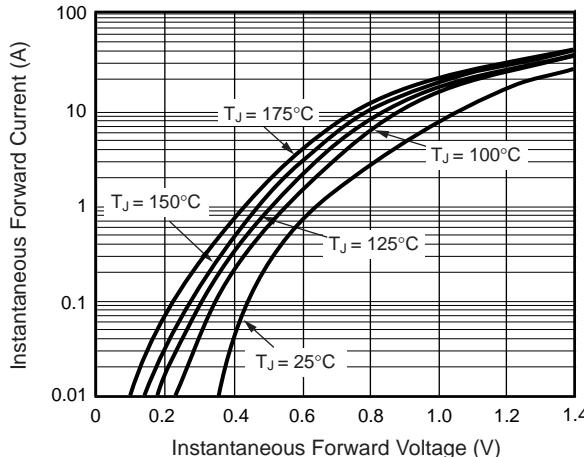


Fig. 3 – Typical Reverse Characteristics

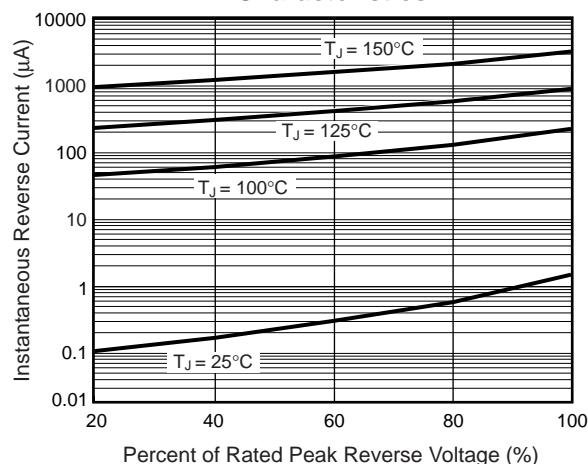


Fig. 4 – Typical Junction Capacitance

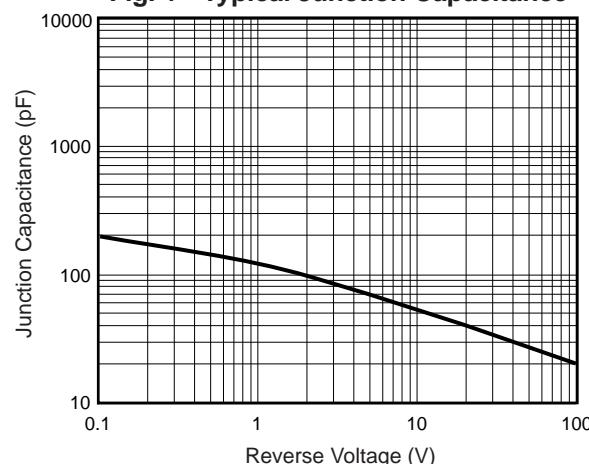


Fig. 5 – Typical Transient Thermal Impedance

